

PCN Number:	20220628000.2	PCN Date:	June 29, 2022
Title:	Qualification of new Fab site (RFAB) using qualified Process Technology, Die Revision, and additional BOM option for select devices		
Customer Contact:	PCN Manager	Dept:	Quality Services
Proposed 1st Ship Date:	Dec 26, 2022	Sample requests accepted until:	July 29, 2022*

***Sample requests received after July 29, 2022 will not be supported.**

Change Type:

<input type="checkbox"/>	Assembly Site	<input type="checkbox"/>	Assembly Process	<input checked="" type="checkbox"/>	Assembly Materials
<input checked="" type="checkbox"/>	Design	<input type="checkbox"/>	Electrical Specification	<input type="checkbox"/>	Mechanical Specification
<input type="checkbox"/>	Test Site	<input type="checkbox"/>	Packing/Shipping/Labeling	<input type="checkbox"/>	Test Process
<input type="checkbox"/>	Wafer Bump Site	<input type="checkbox"/>	Wafer Bump Material	<input type="checkbox"/>	Wafer Bump Process
<input checked="" type="checkbox"/>	Wafer Fab Site	<input checked="" type="checkbox"/>	Wafer Fab Materials	<input checked="" type="checkbox"/>	Wafer Fab Process
		<input type="checkbox"/>	Part number change		

PCN Details

Description of Change:

Texas Instruments is pleased to announce the qualification of a new fab & process technology (RFAB, LBC9) and BOM option for selected devices as listed below in the product affected section. Construction differences are noted below:

Current Fab Site			Additional Fab Site		
Current Fab Site	Process	Wafer Diameter	Additional Fab Site	Process	Wafer Diameter
SFAB	HCMOS	150 mm	RFAB	LBC9	300 mm

The die was also changed as a result of the process change.

Additionally, there will be a BOM/Assembly options introduced for these devices:

	Current	Additional
Bond wire diameter (Cu)	0.96 mils	0.8 mils

The following table provides the updated thermal characteristics to all devices contained within this PCN. All thermal values can be compared to the existing devices by reviewing the datasheets currently on TI.com. The impact to the customer system is anticipated to be negligible, however the customer must review their system design to assess any risk due to the change in thermal characteristics. Please see the table below which provides a summary of thermal values that the devices will be updated to based on each pin/pkg combination.

THERMAL METRIC		PW (TSSOP)	D (SOIC)	DW (SOIC)	UNIT
		14 PINS	16 PINS	20 PINS	
RθJA	Junction-to-ambient thermal resistance	141.0	117.2	109.1	°C/W
RθJC(top)	Junction-to-case (top) thermal resistance	68.8	77.2	76.0	°C/W
RθJB	Junction-to-board thermal resistance	84.2	75.6	77.6	°C/W
ψJT	Junction-to-top characterization parameter	16.9	38.1	51.5	°C/W
ψJB	Junction-to-board characterization parameter	83.6	75.3	77.1	°C/W
RθJC(bot)	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

Reason for Change:

These changes are part of our multiyear plan to transition products from our 150-millimeter factories to newer, more efficient manufacturing processes and technologies, underscoring our commitment to product longevity and supply continuity.

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change	<input checked="" type="checkbox"/> No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
SH-BIP-1	SHE	USA	Sherman
RFAB	RFB	USA	Richardson


Die Rev:

Current

New

Die Rev [2P]	Die Rev [2P]
E,G, -	A, B

Sample product shipping label (not actual product label)


TEXAS INSTRUMENTS
 MADE IN: Malaysia
 2DC: 20:
 MSL '2 /260C/1 YEAR SEAL DT
 MSL 1 /235C/UNLIM 03/29/04
 OPT:
 ITEM: 39
LBL: 5A (L)T0:1750

G4



(1P) SN74LS07NSR
 (Q) 2000 (D) 0336
 (31T) LOT: 3959047MLA
 (4W) TKY(1T) 7523483SI2
 (P)
 (2P) REV: (V) 0033317
 (20L) CS0: SHE (21L) ~~CS0: USA~~
 (22L) ASO: MLA (23L) ACO: MYS

Product Affected:

SN74HCT14QPWRQ1	SN74HC573AQDWRQ1	CD74HC366QDRQ1
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TI Information
Selective Disclosure

Automotive New Product Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)

BD3.5 14PW(TSSOP) Q1 MLA
Approve Date 16-JUNE -2022

Product Attributes

Attributes	Qual Device: SN74HCT14QPWRQ1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: OPA4991QPWRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	-	Signal Chain
Wafer Fab Supplier	RFAB	RFAB	RFAB
Assembly Site	MLA	MLA	MLA
Package Group	TSSOP	TSSOP	TSSOP
Package Designator	PW	PW	PW
Pin Count	14	14	14

- QBS: Qual By Similarity
- Qual Device SN74HCT14QPWRQ1 is qualified at MSL1 260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: SN74HCT14QPWRQ1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: OPA4991QPWRQ1
Test Group A - Accelerated Environment Stress Tests										
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	1 Step	-	3/0/0	3/0/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	110C/85%RH	264 Hours	-	-	3/231/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	-
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	-	-	3/231/0
AC/UHAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	3/231/0	-
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	-	-	1/5/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	3/135/0	3/135/0
Test Group B - Accelerated Lifetime Simulation Tests										
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	-	3/231/0	-
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	150C	300 Hours	1/77/0	-	-
ELFR	B2	AEC Q100-	1	77	Early Life	125C	48	-	3/2400/0	-

		008			Failure Rate			Hours		
Test Group C - Package Assembly Integrity Tests										
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	1/30/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	3/90/0	1/30/0
SD	C3	JEDEC JESD22-B102	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	-
SD	C3	JEDEC JESD22-B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0	-
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	3/30/0	1/10/0
Test Group D - Die Fabrication Reliability Tests										
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests										
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	4000 Volts	1/3/0	-	1/3/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	1500 Volts	1/3/0	-	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100-004	-	1/6/0	1/6/0	3/18/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	3/90/0	3/90/0
Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device	QBS Reference	QBS Reference

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E) : -40C to +150C
- Grade 1 (or Q) : -40C to +125C
- Grade 2 (or T) : -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : ACuHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-NPD-2203-018

Automotive New Product Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)

BD3 HC PCN Devices : D Automotive
Approve Date 13-JUNE -2022

Product Attributes

Attributes	Qual Device: CD74HC366QDRQ1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: SN74HCS74QDRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Logic	-	Logic
Wafer Fab Supplier	RFAB	RFAB	RFAB
Assembly Site	MLA	MLA	MLA
Package Group	SOIC	TSSOP	SOIC
Package Designator	D	PW	D
Pin Count	16	14	14

- QBS: Qual By Similarity
- Qual Device CD74HC366QDRQ1 is qualified at MSL1 250C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: CD74HC366QDRQ1	QBS Reference: SN74HCS74QPWRQ1	QBS Reference: SN74HCS74QDRQ1
Test Group A - Accelerated Environment Stress Tests										
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL1 260C	1 Step	-	3/0/0	3/0/0
HAST	A2	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0
ACU/HAST	A3	JEDEC JESD22-A102/JEDEC JESD22-A118	3	77	Unbiased HAST	130C/85%RH	96 Hours	-	3/231/0	3/231/0
TC	A4	JEDEC JESD22-A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	-	3/231/0	3/231/0
HTSL	A6	JEDEC JESD22-A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	3/135/0	3/135/0
Test Group B - Accelerated Lifetime Simulation Tests										
HTOL	B1	JEDEC JESD22-A108	1	77	Life Test	125C	1000 Hours	-	3/231/0	3/231/0
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-
Test Group C - Package Assembly Integrity Tests										
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	-	3/90/0	3/90/0

SD	C3	JEDEC JESD22-B102	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	3/45/0
SD	C3	JEDEC JESD22-B102	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0	3/45/0
PD	C4	JEDEC JESD22-B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	3/30/0	3/30/0
Test Group D - Die Fabrication Reliability Tests										
EM	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group E - Electrical Verification Tests										
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	4000 Volts	1/3	1/3/0	1/3/0
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	1500 Volts	1/3	1/3/0	1/3/0
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	1/6	1/6/0	1/6/0
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90	3/90/0	3/90/0

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV : 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E) : -40C to +150C
- Grade 1 (or Q) : -40C to +125C
- Grade 2 (or T) : -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: <http://www.ti.com/>

TI Qualification ID: R-CHG-2202-015

**Automotive New Product Qualification Summary
(As per AEC-Q100 and JEDEC Guidelines)**

BD3 HC/HCT PCN Devices: 20DW Automotive Device (MLA) SN74HC573AQDWRQ1 & CD74HCT688M96

Approved 13-Jun-2022

Product Attributes

Attributes	Qual Device: SN74HC573AQDWRQ1	QBS Process Reference: SN74HC574QPWRQ1	QBS Package Reference: SN74HC574QDRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range	-40 to +125 C	-40 to +125 C	-40 to +125 C
Product Function	Logic	Logic	Logic
Wafer Fab Supplier	RFAB	RFAB	RFAB
Die Revision	A0	B1	B1
Assembly Site	MLA	MLA	MLA
Package Type	SOIC	TSSOP	SOIC
Package Designator	DW	PW	D
Ball/Lead Count	20	14	14

- QBS: Qual By Similarity

- Qual Device SN74HC573AQDWRQ1 is qualified at LEVEL1-260C

Qualification Results

Data Displayed as: Number of lots / Total sample size / Total failed

Type	#	Test Spec	Min Lot Qty	SS/Lot	Test Name / Condition	Duration	Qual Device: SN74HC573AQDWRQ1	QBS Process Reference: SN74HC574QPWRQ1	QBS Package Reference: SN74HC574QDRQ1
Test Group A – Accelerated Environment Stress Tests									
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	Level 1-260C	No Fails	No Fails	No Fails
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0	3/231/0	3/231/0
AC	A3	JEDEC JESD22- A102	3	77	Autoclave 121C	96 Hours	3/231/0	3/231/0	3/231/0
TC	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, - 65/150C	500 Cycles	3/231/0	3/231/0	3/231/0
PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle	1000 Cycles	N/A	-	-
HTSL	A6	JEDEC JESD22- A103	1	45	High Temp Storage Bake 150C	1000 Hours	1/45/0	3/135/0	3/135/0
Test Group B – Accelerated Lifetime Simulation Tests									
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test, 125C	1000 Hours	3/231/0	-	-
HTOL	B1	JEDEC JESD22- A108	3	77	Life Test, 150C	300 Hours	-	3/231/0	1/77/0
ELFR	B2	AEC Q100-008	3	800	Early Life Failure Rate, 125C	48 Hours	-	3/2400/0	-
EDR	B3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A	-	-
Test Group C – Package Assembly Integrity Tests									
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk> 1.67	3/90/0	3/90/0	3/90/0
SD	C3	JEDEC JESD22- B102	1	15	Pb Free Surface Mount Solderability	8 Hours Steam Age	-	3/45/0	3/45/0
SD	C3	JEDEC JESD22- B102	1	15	Surface Mount Solderability >95% Lead Coverage	-	-	3/45/0	3/45/0
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67	-	3/90/0	3/90/0

Test Group D – Die Fabrication Reliability Tests									
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements	-	-
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements	-	-
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements	-	-
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements	-	-
SM	D5	-	-	-	Stress Migration	-	Completed Per Process Technology Requirements	-	-
Test Group E – Electrical Verification Tests									
HBM	E2	AEC Q100-002	1	3	ESD - HBM - Q100	4000V	1/3/0	-	-
CDM	E3	AEC Q100-011	1	3	ESD - CDM - Q100	1500V	1/3/0	1/3/0	-
LU	E4	AEC Q100-004	1	6	Latch-up	(Per AEC-Q100-004)	1/6/0	1/6/0	1/6/0
LU	E4	AEC Q100-004	1	6	Latch-up	Elec Test-1	1/6/0	-	-
ED	E5	AEC Q100-009	3	30	Auto Electrical Distributions	Cpk>1.67 Room, hot, and cold test	3/90/0	3/90/0	3/90/0

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C
Grade 1 (or Q): -40°C to +125°C
Grade 2 (or T): -40°C to +105°C
Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold: HTOL, ED
Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
Room: AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

TI Qualification ID: 20210126-138368

For questions regarding this notice, e-mails can be sent to the contacts shown below or your local Field Sales Representative.

Location	E-Mail
WW Change Management Team	PCN_ww_admin_team@list.ti.com

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